

DCR1008SF

PHASE CONTROL THYRISTOR

APPLICATIONS

- High Power Drives.
- High Voltage Power Supplies.
- DC Motor Control.
- Welding.
- Battery Chargers.

KEY PARAMETERS

V_{DRM}	3600V
$I_{T(AV)}$	830A
I_{TSM}	15000A
dV/dt^*	1000V/μs
di/dt	200A/μs

*Higher dV/dt selections available

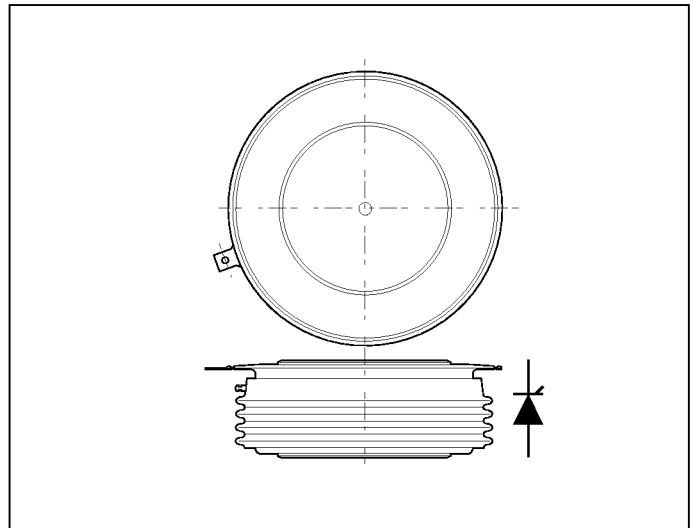
FEATURES

- Double Side Cooling.
- High Surge Capability.

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V_{DRM} V_{RRM} V	Conditions
DCR1008SF36	3600	$T_{vj} = 0^\circ$ to 125° C, $I_{DRM} = I_{RRM} = 150$ mA, $V_{DRM}, V_{RRM} t_p = 10$ ms, V_{DSM} & $V_{RSM} =$ V_{DRM} & $V_{RRM} + 100$ V Respectively
DCR1008SF35	3500	
DCR1008SF34	3400	
DCR1008SF33	3300	
DCR1008SF32	3200	

Lower voltage grades available.



Outline type code: F. See package outline for further information.

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load, $T_{case} = 80^\circ$ C	830	A
$I_{T(RMS)}$	RMS value	$T_{case} = 80^\circ$ C	1300	A
I_T	Continuous (direct) on-state current	$T_{case} = 80^\circ$ C	1160	A
Single Side Cooled (Anode side)				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load, $T_{case} = 80^\circ$ C	565	A
$I_{T(RMS)}$	RMS value	$T_{case} = 80^\circ$ C	890	A
I_T	Continuous (direct) on-state current	$T_{case} = 80^\circ$ C	770	A

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SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine; $T_{case} = 125^{\circ}C$	12.0	kA
I^2t	I^2t for fusing	$V_R = 50\% V_{RRM}$ - 1/4 sine	0.72×10^6	A ² s
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine; $T_{case} = 125^{\circ}C$	15.0	kA
I^2t	I^2t for fusing	$V_R = 0$	1.125×10^6	A ² s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions	Min.	Max.	Units	
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.022	$^{\circ}C/W$
		Single side cooled	Anode dc	-	0.038	$^{\circ}C/W$
			Cathode dc	-	0.052	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 19.5kN with mounting compound	Double side	-	0.004	$^{\circ}C/W$
			Single side	-	0.008	$^{\circ}C/W$
T_{vj}	Virtual junction temperature	On-state (conducting)		-	135	$^{\circ}C$
		Reverse (blocking)		-	125	$^{\circ}C$
T_{slg}	Storage temperature range		-55	125	$^{\circ}C$	
-	Clamping force		18.0	22.0	kN	

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions	Typ.	Max.	Units	
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM} , $T_{case} = 125^{\circ}C$	-	150	mA	
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125^{\circ}C$.	-	1000	V/ μ s	
dI/dt	Rate of rise of on-state current	From 67% V_{DRM} , $I_T = 1500A$, Gate source 1.5A $t_r \leq 0.5\mu$ s. $T_j = 125^{\circ}C$.	Repetitive 50Hz	-	75	A/ μ s
			Non-repetitive	-	200	A/ μ s
$V_{T(TO)}$	Threshold voltage	At $T_{vj} = 125^{\circ}C$	-	1.1	V	
r_T	On-state slope resistance	At $T_{vj} = 125^{\circ}C$	-	0.57	m Ω	
t_{gd}	Delay time	$V_D = 67\% V_{DRM}$, Gate source 30V, 15 Ω Rise time 0.5 μ s, $T_j = 25^{\circ}C$	-	2.0	μ s	
I_L	Latching current	$T_j = 25^{\circ}C$, $V_D = 5V$	350	900	mA	
I_H	Holding current	$T_j = 25^{\circ}C$, $R_{g-k} = \infty$	230	600	mA	
t_q	Turn-off time	$I_T = 3000A$, $t_p = 1ms$, $T_j = 125^{\circ}C$, $V_{RM} = 900V$, $dI_{RR}/dt = 5A/\mu$ s, $V_{DR} = 2800V$, $dV_{DR}/dt = 20V/\mu$ s linear	-	500	μ s	

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	3.5	V
I_{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	200	mA
V_{GD}	Gate non-trigger voltage	At V_{DRM} , $T_{case} = 125^{\circ}C$	0.25	V
V_{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	V
V_{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	V
V_{RGM}	Peak reverse gate voltage		5	V
I_{FGM}	Peak forward gate current	Anode positive with respect to cathode	30	A
P_{GM}	Peak gate power	See table. fig. 4	150	W
$P_{G(AV)}$	Mean gate power		10	W

CURVES

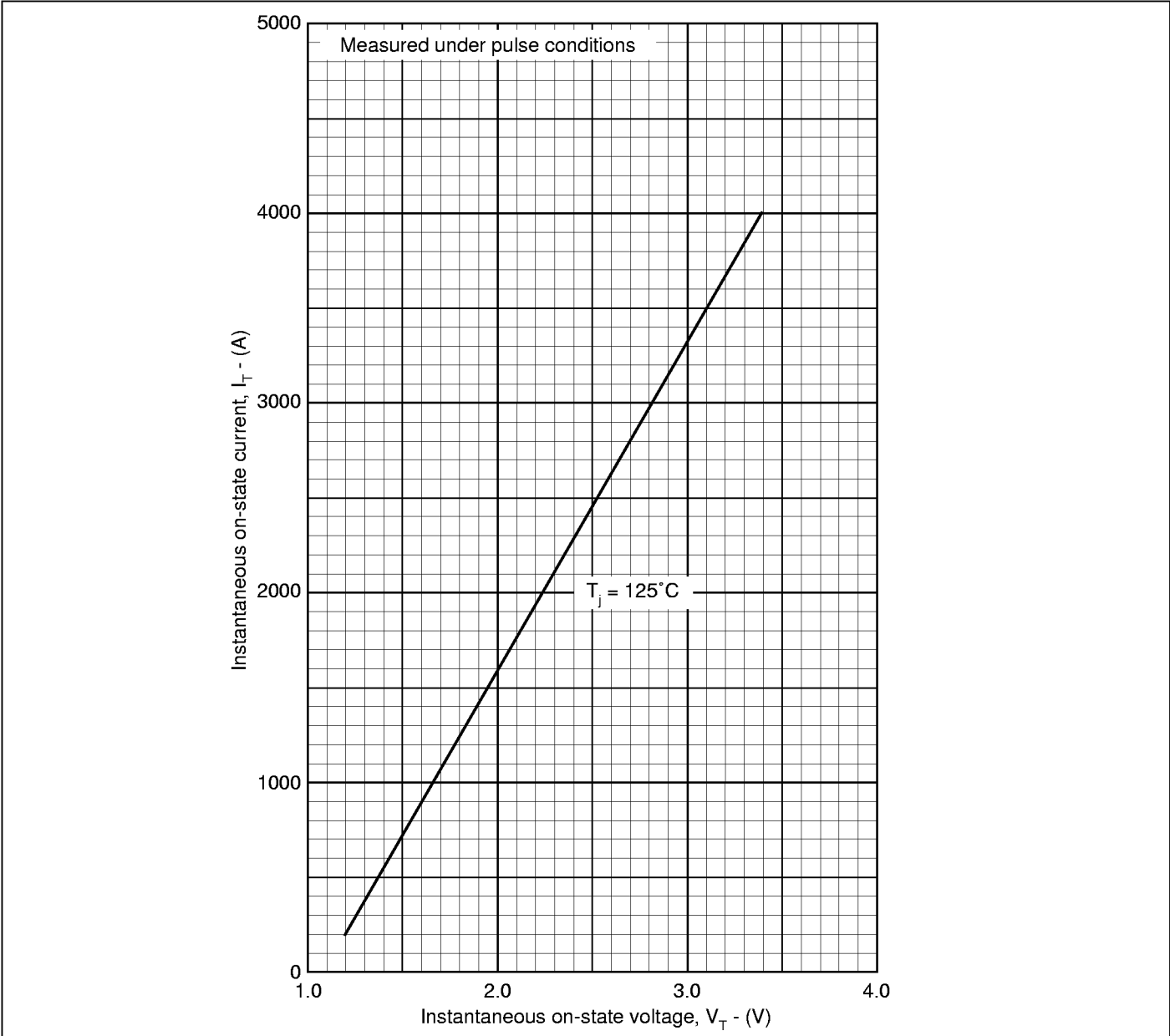


Fig.1 Maximum (limit) on-state characteristics

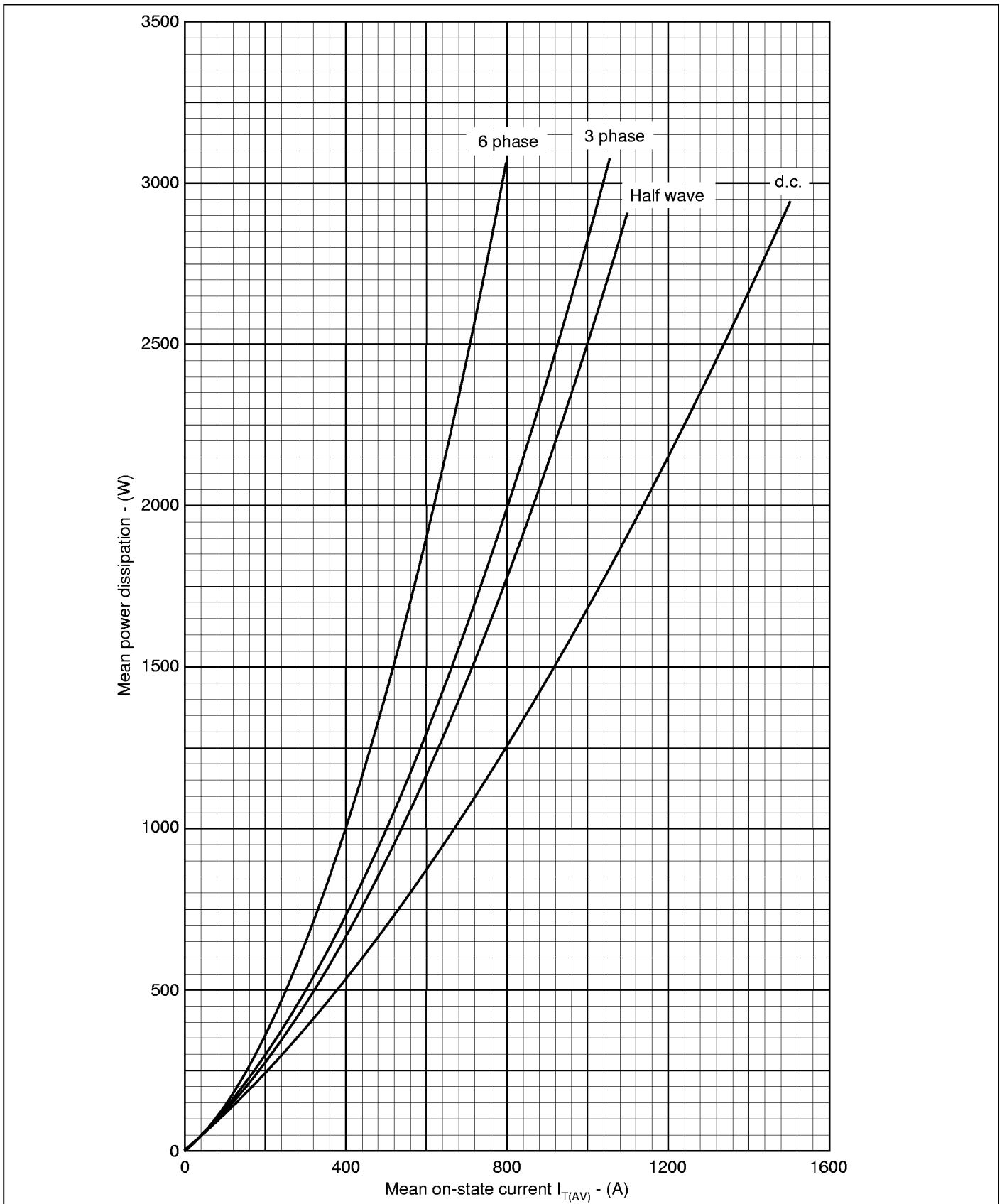


Fig.2 Dissipation curves

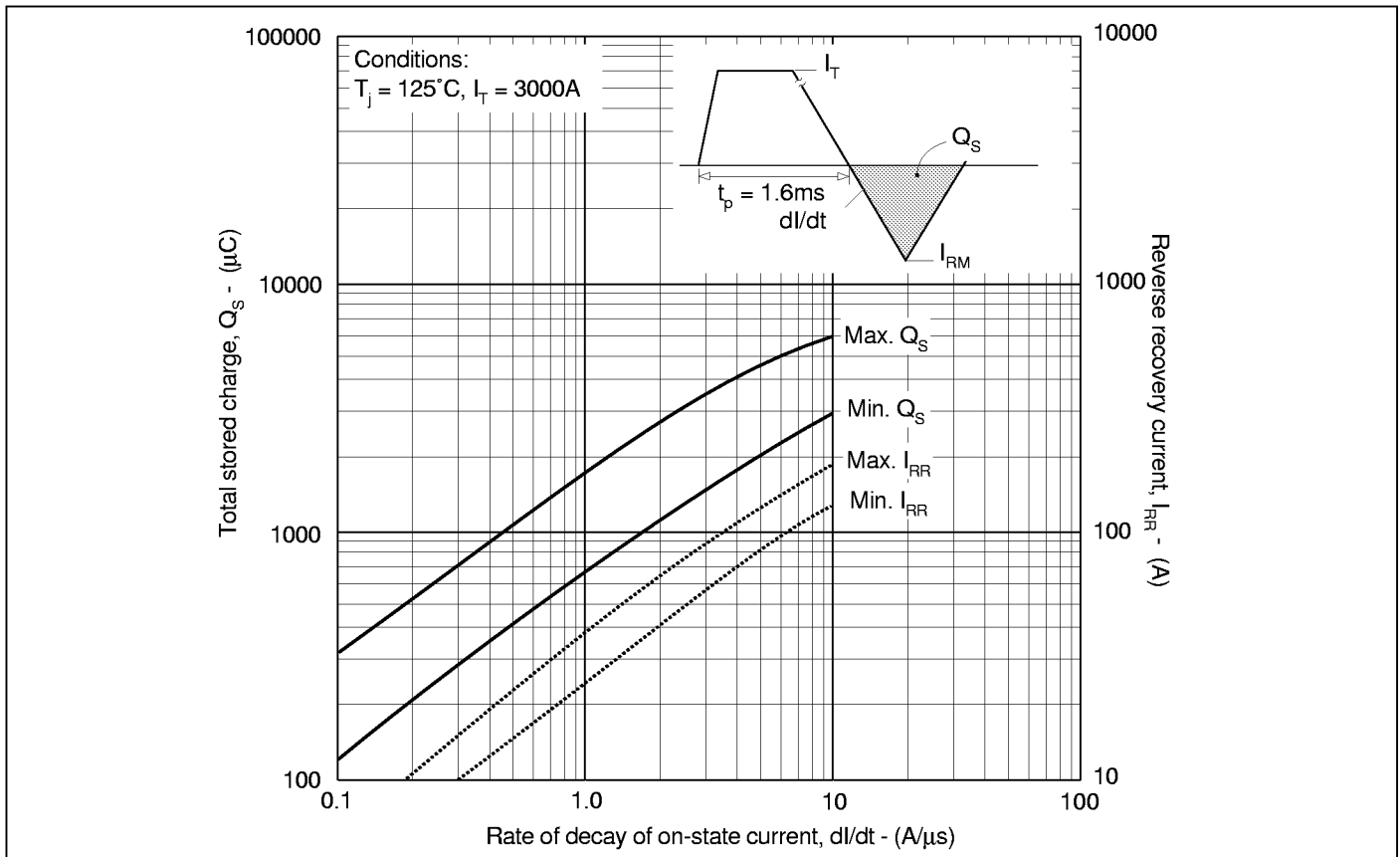


Fig.3 Stored charge

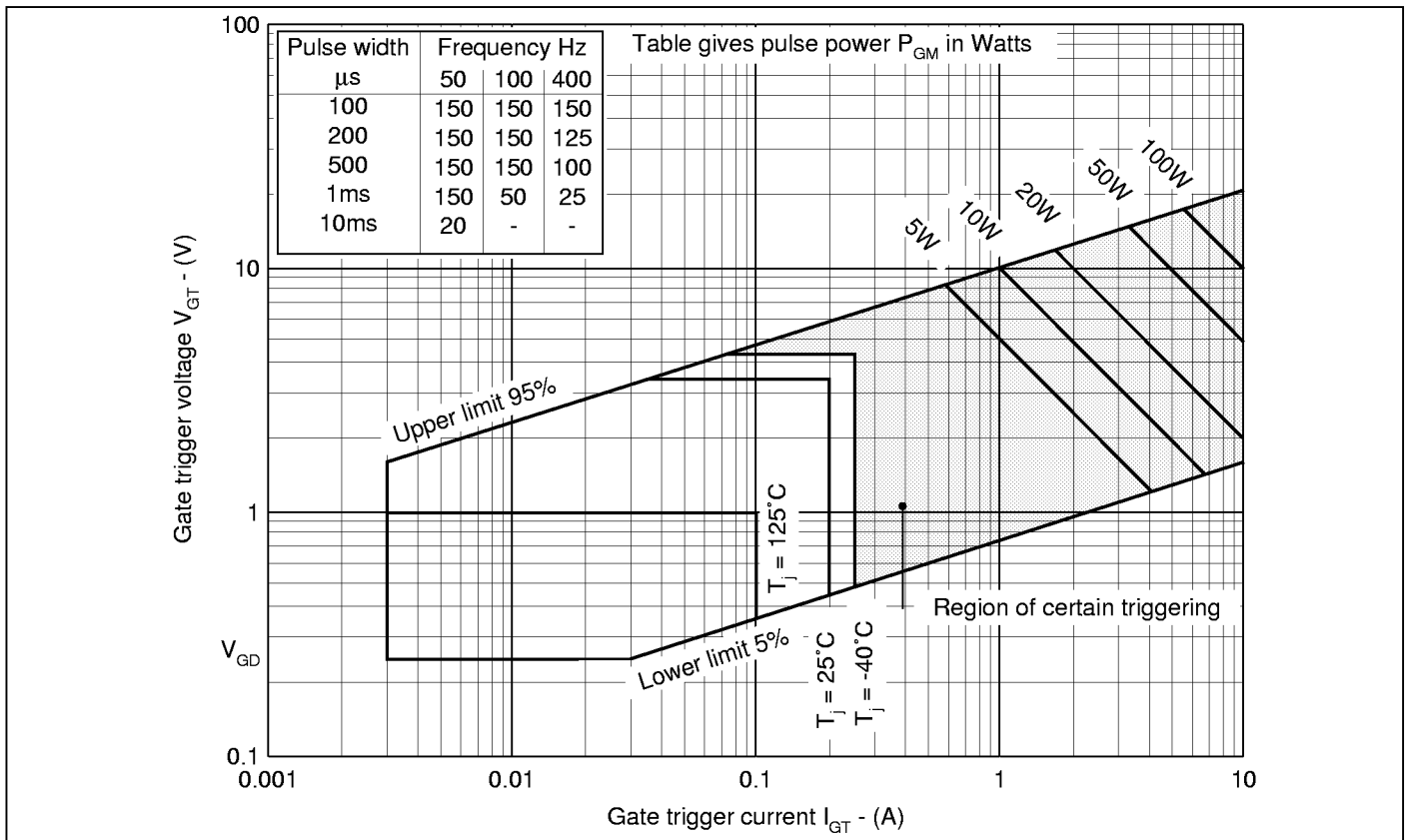


Fig.4 Gate characteristics

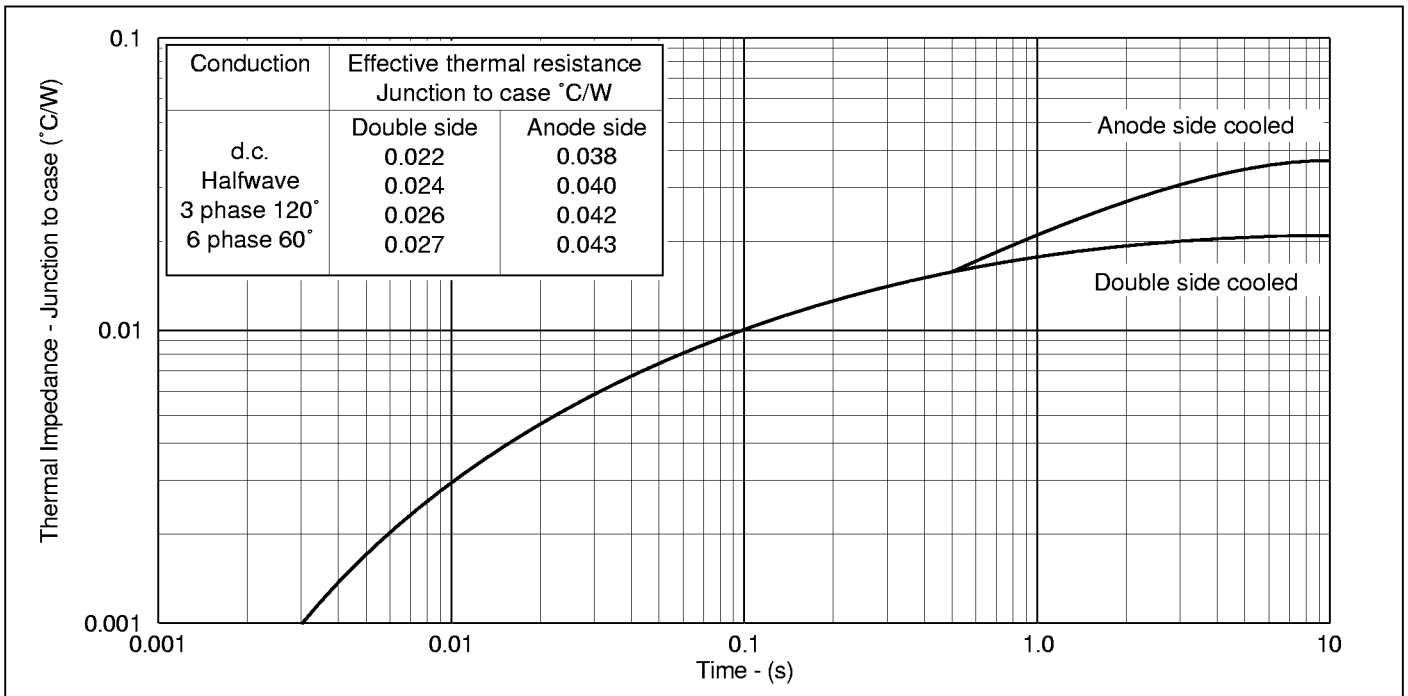


Fig. Transient thermal impedance - junction to case - (°C/W)

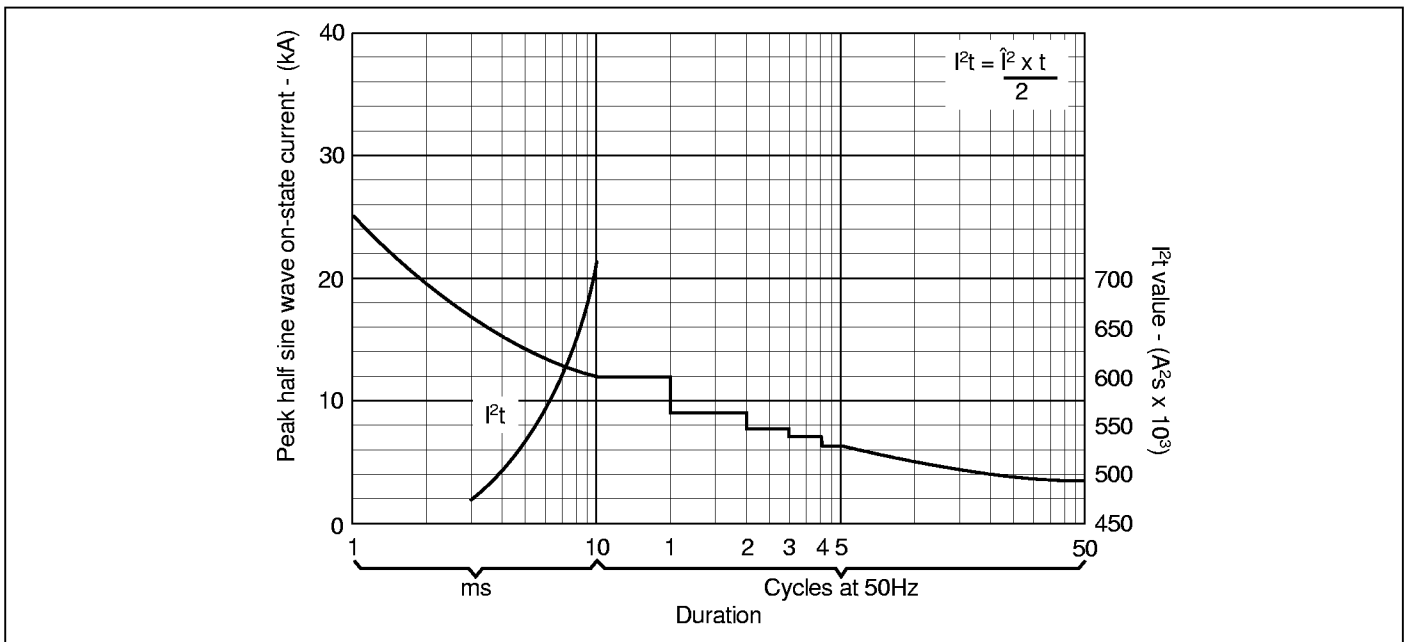
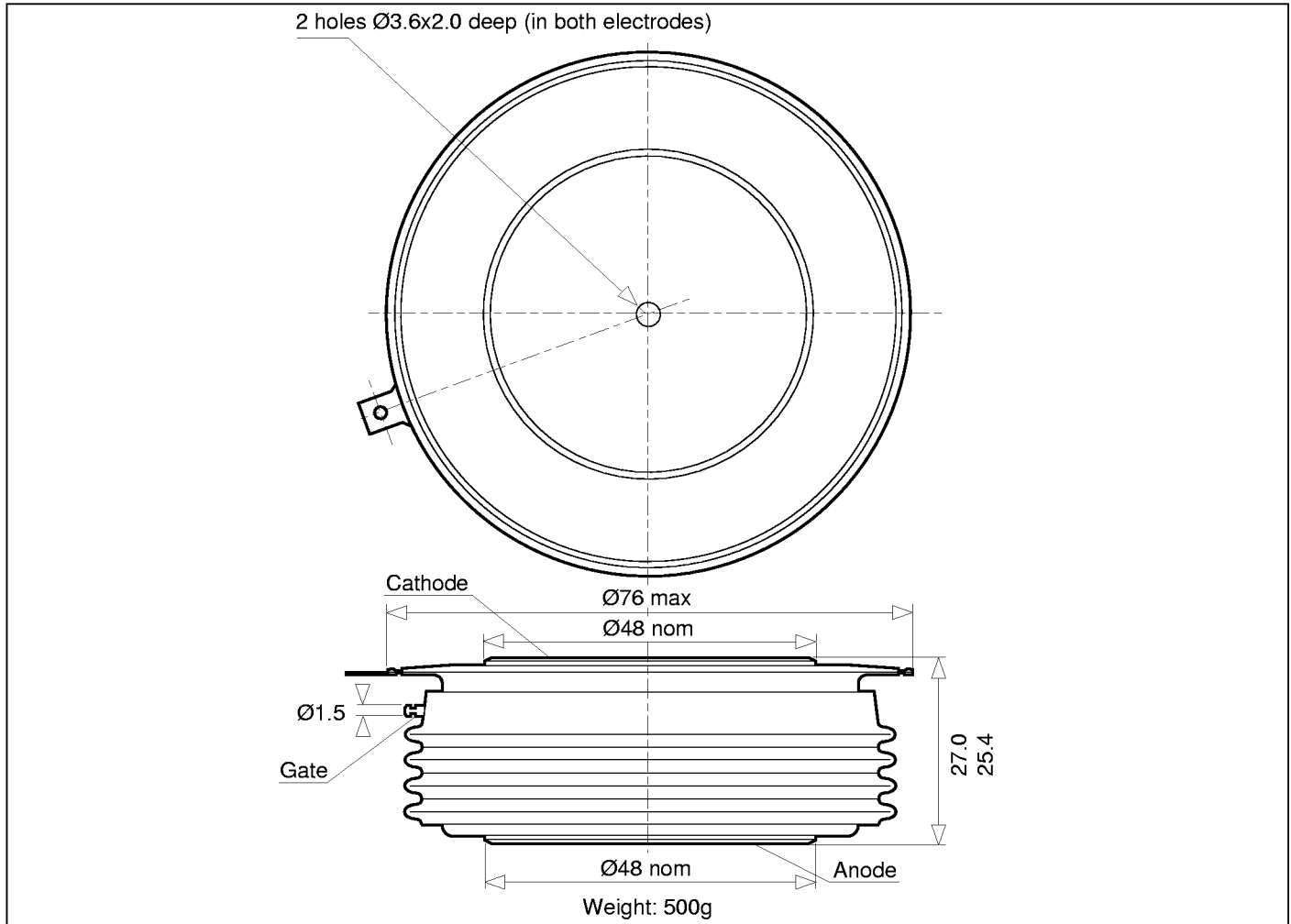


Fig.6 Surge (non-repetitive) on-state current vs time (with 50% V_{RRM} at $T_{case} = 125^\circ C$)

DCR1008SF

PACKAGE OUTLINE - F

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



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